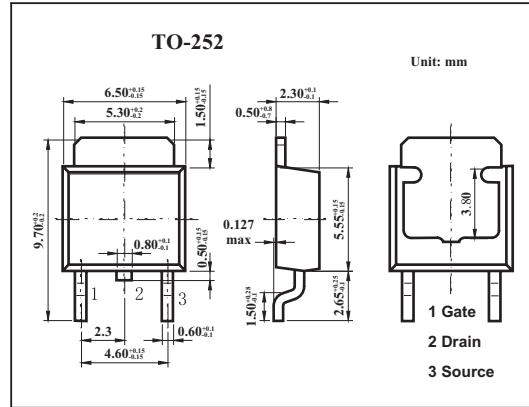
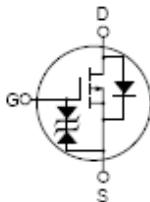


MOS Field Effect Transistor

2SJ600

■ Features

- Low on-resistance
 $R_{DS(on)1} = 50 \text{ m}\Omega$ MAX. ($V_{GS} = -10 \text{ V}$, $I_D = -13 \text{ A}$)
 $R_{DS(on)2} = 79 \text{ m}\Omega$ MAX. ($V_{GS} = -4.0 \text{ V}$, $I_D = -13 \text{ A}$)
- Low Ciss: $C_{iss} = 1900 \text{ pF TYP.}$
- Built-in gate protection diode



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	-60	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current (DC)	I_D	± 25	A
Drain current(pulse) *	I_D	± 70	A
Power dissipation	P_D	45	W
$T_c=25^\circ\text{C}$			
$T_a=25^\circ\text{C}$	P_D	1.0	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leqslant 10 \mu\text{s}$, duty cycle $\leqslant 1\%$

2SJ600

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	Idss	Vds=-60V,Vgs=0			-10	µ A
Gate leakage current	IGSS	Vgs=±20V,Vds=0			±10	µ A
Gate to source cutoff voltage	Vgs(off)	Vds=-10V,Id=-1mA	1.5	2.0	2.5	V
Forward transfer admittance	Yfs	Vds=-10V,Id=-13A	10	20		S
Drain to source on-state resistance	Rds(on)	Vgs=-10V,Id=-13A		41	50	mΩ
		Vgs=-4.0V,Id=-13A		55	79	mΩ
Input capacitance	Ciss	Vds=-10V,Vgs=0,f=1MHZ		1900		pF
Output capacitance	Coss			350		pF
Reverse transfer capacitance	Crss			140		pF
Turn-on delay time	td(on)	Vgs(on)=-10V,Id=-13A ,Vdd=-30V,Rg=0Ω		9		ns
Rise time	tr			10		ns
Turn-off delay time	td(off)			67		ns
Fall time	tf			19		ns
Total Gate Charge	Qg	Id = -25A Vdd= -48 V Vgs =-10 V		38		nC
Gate to Source Charge	Qgs			7		nC
Gate to Drain Charge	Qgd			10		nC
Body Diode Forward Voltage	Vf(s-d)	IF = -25A, Vgs = 0 V		1.0		V
Reverse Recovery Time	trr	IF = -25 A, Vgs = 0 V di/dt = 100 A / µ s		49		ns
Reverse Recovery Charge	Qrr			100		nC